



09/988984

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Docket No.: M4065.0608/P608
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
John T. Moore et al.

Patent No.: 6,815,818

Issued: November 9, 2004

For: ELECTRODE STRUCTURE FOR USE IN AN
INTEGRATED CIRCUIT

**REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR § 1.322**

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Certificate
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of Correction

Dear Sir:

Upon reviewing the above-identified patent, Patentees noted omissions and a typographical error which should be corrected.

In the **Specification**: Column 11, line 10, "for" should read --form--.

In **Item (56) (References Cited)**: The non-patent literature cited during prosecution of the application (No. 09/988,984) has not been listed. The non-patent literature was considered during prosecution. Attached are Examiner-initialed and returned copies of eight relevant pages listing 174 references from Applicants' Forms PTO/SB/08A submitted with Information Disclosure Statements dated October 16, 2002 and May 20, 2003.

The errors were not in the application as filed or amended by Applicants. Accordingly no fee is believed to be required.

MAY 15 2006

Transmitted herewith is a proposed Certificate of Correction effecting such corrections. Patentees respectfully solicit the granting of the requested Certificate of Correction.

Dated: May 11, 2006

Respectfully submitted,

By 

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Registration No.: 28,371

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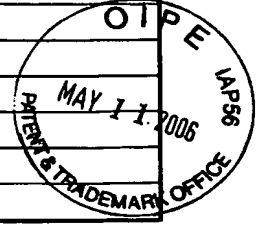
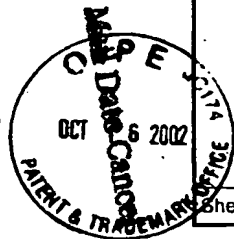
INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2 of 8

Complete if Known

Application Number	09/988,984
Filing Date	November 19, 2001
First Named Inventor	John T. Moore
Group Art Unit	2812-2823
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608



OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Sheet	3	of	8	Attorney Docket Number	M4065.0608/P608
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First Named Inventor	John T. Moore
Group Art Unit	2842 2823
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608

Sheet	4	of	8
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Tup	CO3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of $\text{Ag}_x(\text{GeSe}_3)_{1-x}$ ($0 < x < 0.571$) glasses, Solid state Ionics 123 (1999) 259-269.	
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Tup	CT3	Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTi chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.	
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Sheet	7	of	8	Attorney Docket Number	M4065.0608/P608
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Complete if Known

Application Number	09/988,984
Filing Date	November 19, 2001
First Named Inventor	John T. Moore
Group Art Unit	2012 28 23
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608

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 Sheet 8 of 8
Complete if Known

Application Number	09/988,984
Filing Date	November 19, 2001
First Named Inventor	John T. Moore
Group Art Unit	2842-2823
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0608/P608

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Examiner Signature	<i>Shamir</i>	Date Considered	3/2/2002
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Substitute for form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	09/988,984
		Filing Date	November 19, 2001
		First Named Inventor	John T. Moore
		Art Unit	2812 2823
		Examiner Name	Not Yet Assigned T. PHAM
		Attorney Docket Number	M4065.0608/P608
Sheet	4	of	4

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TUP	CA	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp. 1-6 (Pre-May 2000).	
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	CP		
	CQ		

Examiner Signature		Date Considered	7/21/03
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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,815,818
DATED : November 9, 2004
INVENTOR(S) : John T. Moore et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 11, line 10, "for" should read --form--.

Item (56) (References Cited) should include the following cited art:

Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: *Programmable Metalization Cell(PMC)*, pp. 1-6 (Pre-May 2000).

Helbert et al., *Intralevel hybrid resist process with submicron capability*, SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).

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MAILING ADDRESS OF SENDER:
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Kolobov and Elliott, Photodoping of Amorphous Chalcogenides by Metals, Advances in Physics, Vol. 40, No 5, 625-684 (1991).

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Shimizu et al., *The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses*, 46 B. CHEM SOC. JAPAN, No. 12, pp. 3662-3365 (1973).

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Item (56) (References Cited) -- continued

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Item (56) (References Cited) -- continued

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PATENT NO. 6,815,818

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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

PATENT NO. : 6,815,818
DATED : November 9, 2004
INVENTOR(S) : John T. Moore et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Item (56) (References Cited) -- continued

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